Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Single-Output LDO Regulators

Ultra Low Quiescent Current LDO Regulator

BD7xxL2EFJ/FP/FP3-C

●General Description

The BD7xxL2EFJ/FP/FP3-C are low quiescent regulators featuring 50V absolute maximum voltage, and output voltage accuracy of ±2%, 200mA output current and 6μA (Typ) current consumption. These regulators are therefore ideal for applications requiring a direct connection to the battery and a low current consumption. Ceramic capacitors can be used for compensation of the output capacitor phase. Furthermore, these ICs also feature overcurrent protection to protect the device from damage caused by short-circuiting and an integrated thermal shutdown to protect the device from overheating at overload conditions.

●Features

- Ultra low quiescent current: 6μA (Typ)
- Output current capability: 200mA
- Output voltage: 3.3 V or 5.0 V(Typ)
- High output voltage accuracy: ±2%
- Low saturation voltage by using PMOS output transistor.
- Integrated overcurrent protection to protect the IC from damage caused by output short-circuiting.
- Integrated thermal shutdown to protect the IC from overheating at overload conditions.
- Low ESR ceramic capacitor can be used as output capacitor.
- HTSOP-J8, TO252-3, SOT223-4(F) (*1) 3type package
  (*1 : SOT223-4、SOT223-4F)

●Key specification

Ultra low quiescent current:	6μA (Typ)
Output voltage:	3.3 V or 5.0 V (Typ)
Output current capability:	200mA
High output voltage accuracy:	±2%
Low ESR ceramic capacitor can be used as output capacitor	
AEC-Q100 Qualified(*2) (*2:Grade1)	

●Packages

	W (Typ) x D (Typ) x H (Max)
EFJ: HTSOP-J8	4.90mm x 6.00mm x 1.00mm
FP: TO252-3	6.50mm x 9.50mm x 2.50mm
FP3 : SOT223-4(F)	6.53mm x 7.00mm x 1.80mm

Figure 1. Package Outlook

●Applications

- Automotive (body, audio system, navigation system, etc.)

●Typical Application Circuits

- Components externally connected: 0.1 μF ≤ CIN, 4.7 μF ≤ COUT (Min)
  *Electrolytic, tantalum and ceramic capacitors can be used.

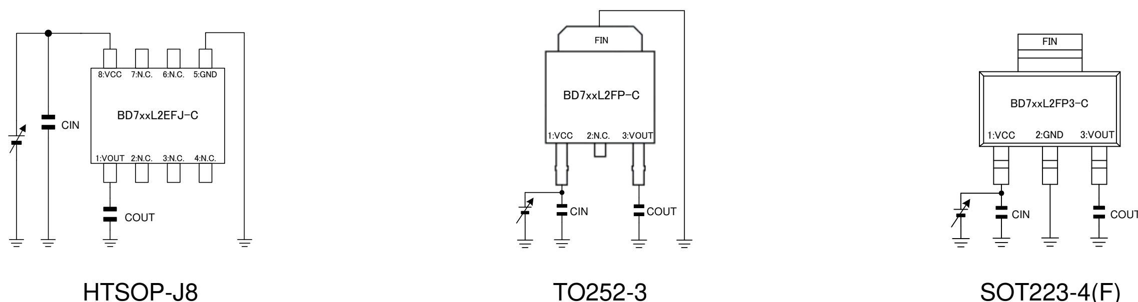
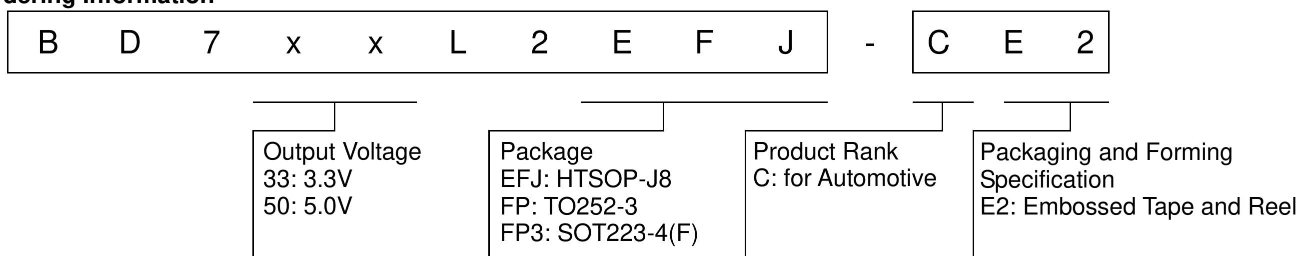


Figure 2. Typical Application Circuits

○Product structure : Silicon monolithic integrated circuit ○This product is not designed protection against radioactive rays

© 2013 ROHM Co., Ltd. All rights reserved.

●Ordering Information



●Lineup

Output current ability	Output voltage (Typ)	Package type	Orderable Part Number
200 mA	3.3 V	HTSOP-J8	BD733L2EFJ-CE2
		TO252-3	BD733L2FP-CE2
		SOT223-4(F)	BD733L2FP3-CE2
	5.0 V	HTSOP-J8	BD750L2EFJ-CE2
		TO252-3	BD750L2FP-CE2
		SOT223-4(F)	BD750L2FP3-CE2

© 2013 ROHM Co., Ltd. All rights reserved.

●Pin Configuration

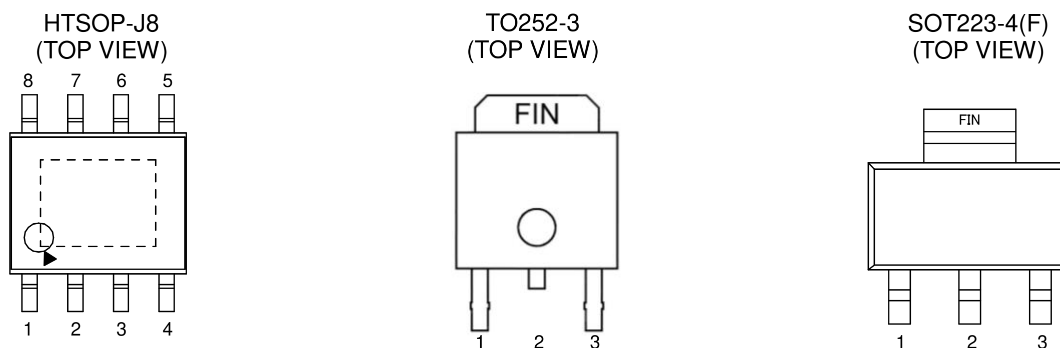


Figure 3. Pin Configuration

●Pin Description

■HTSOP-J8

Pin No.	Pin Name	Function
1	VOUT	Output pin
2	N.C.	Not connected
3	N.C.	Not connected
4	N.C.	Not connected
5	GND	GND
6	N.C.	Not connected
7	N.C.	Not connected
8	VCC	Supply voltage input pin

(※N.C. terminals are not need to connect to GND.
(※Exposed die pad is need to be connected to GND in the inside of IC.)
(※Exposed die pad is connected to GND in the inside of IC.)

■TO252-3, SOT223-4(F)

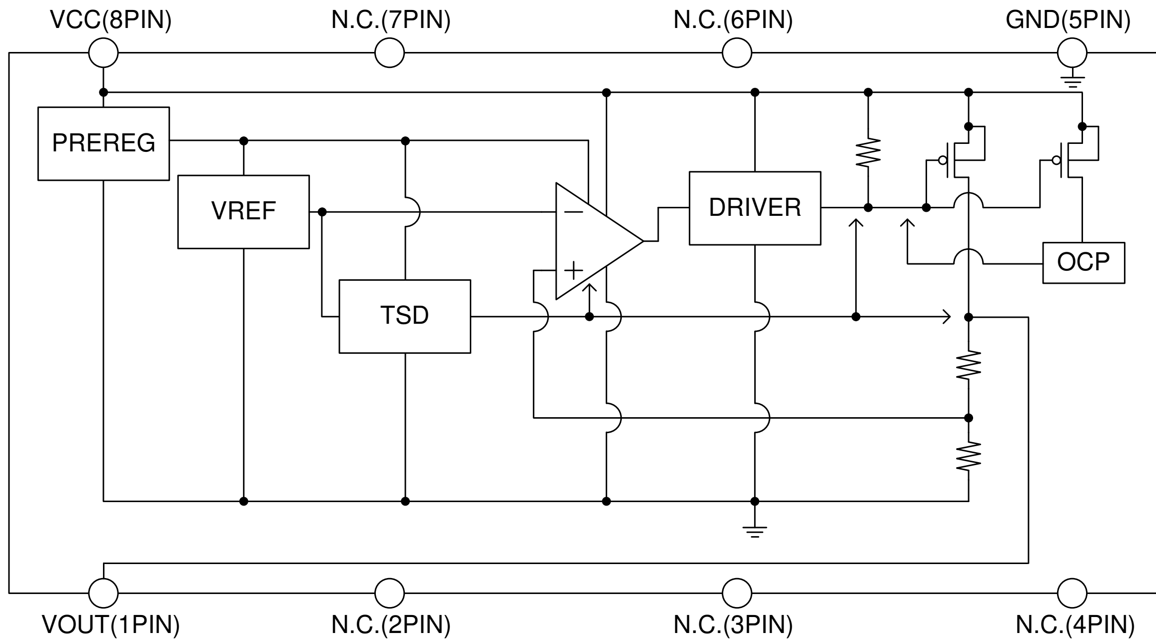
Pin No.	Pin Name	Function
1	VCC	Supply voltage input pin
2	N.C./GND	TO252-3: N.C. SOT223-4(F): GND
3	VOUT	Output pin
FIN	GND	GND

(※N.C. terminals are not need to connect to GND.)

© 2013 ROHM Co., Ltd. All rights reserved.

●Block Diagram

■HTSOP-J8



■TO252-3, SOT223-4(F)

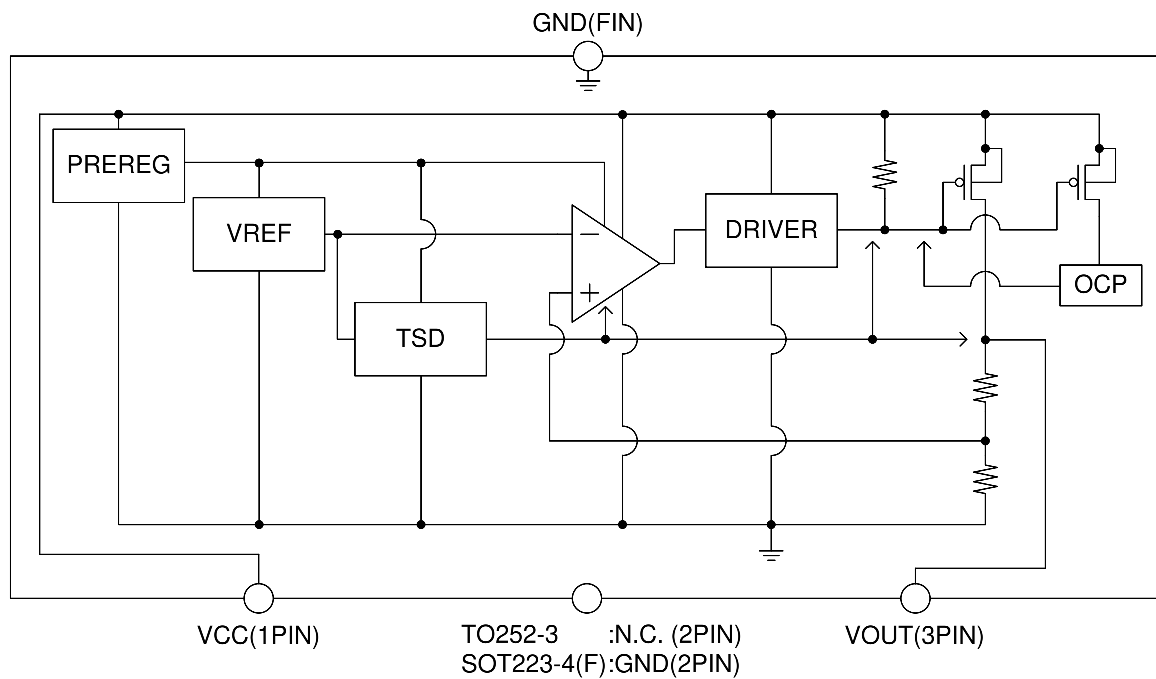


Figure 4. Block Diagram

© 2013 ROHM Co., Ltd. All rights reserved.

●Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Supply Voltage *1	VCC	-0.3 to +50.0	V
Operating Temperature Range	Topr	-40 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Maximum Junction Temperature	Tjmax	150	°C

*1 Pd should not be exceeded.

●Operating Conditions (-40 < Ta < +125°C)

■BD733L2EFJ/FP/FP3-C

Parameter	Symbol	Min	Max	Unit
Supply Voltage *2	VCC	4.37	45.0	V
Startup Voltage *3	VCC	3.0	-	V
Output Current	IOUT	0	200	mA

■BD750L2EFJ/FP/FP3-C

Parameter	Symbol	Min	Max	Unit
Supply Voltage *2	VCC	5.8	45.0	V
Startup Voltage *3	VCC	3.0	-	V
Output Current	IOUT	0	200	mA

*2 For output voltage, refer to the dropout voltage corresponding to the output current.
*3 When IOUT=0mA.

© 2013 ROHM Co., Ltd. All rights reserved.

● **Thermal Resistance**(*1)

Parameter	Symbol	Thermal Resistance (Typ)		Unit
		1s(*3)	2s2p(*4)	
HTSOP-J8				
Junction to Ambient	θ_{JA}	130	34	°C/W
Junction to Top Characterization Parameter(*2)	Ψ_{JT}	15	7	°C/W
TO252-3				
Junction to Ambient	θ_{JA}	136	23	°C/W
Junction to Top Characterization Parameter(*2)	Ψ_{JT}	17	3	°C/W
SOT223-4(F)				
Junction to Ambient	θ_{JA}	164	71	°C/W
Junction to Top Characterization Parameter(*2)	Ψ_{JT}	20	14	°C/W

(*1)Based on JESD51-2A(Still-Air).
(*2)The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.
(*3)Using a PCB board based on JESD51-3.

Layer Number of Measurement Board	Material	Board Size
Single	FR-4	114.3mm x 76.2mm x 1.57mmt

Top	
Copper Pattern	Thickness
Footprints and Traces	70μm

(*4)Using a PCB board based on JESD51-5, 7.

Layer Number of Measurement Board	Material	Board Size	Thermal Via(*5)	
			Pitch	Diameter
4 Layers	FR-4	114.3mm x 76.2mm x 1.6mmt	1.20mm	Φ0.30mm

Top		2 Internal Layers		Bottom	
Copper Pattern	Thickness	Copper Pattern	Thickness	Copper Pattern	Thickness
Footprints and Traces	70μm	74.2mm x 74.2mm	35μm	74.2mm x 74.2mm	70μm

(*5) This thermal via connects with the copper pattern of all layers.

© 2013 ROHM Co., Ltd. All rights reserved.

●**Electrical Characteristics (BD733L2EFJ/FP/FP3-C)**

(Unless otherwise specified, -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA, Reference value: Ta=25°C)

Parameter	Symbol	Limit			Unit	Conditions
		Min	Typ	Max		
Bias current	Ib	-	6	15	μA	
Output voltage	VOUT	3.23	3.30	3.37	V	8V < VCC < 16V 0mA < IOUT < 100mA
Dropout voltage	ΔVd	-	0.6	1.0	V	VCC=VOUT×0.95, IOUT=200mA
Ripple rejection	R.R.	50	63	-	dB	f=120Hz, ein=1Vrms, IOUT=100mA
Line regulation	Reg I	-	5	20	mV	8V < VCC < 16V
Load regulation	Reg L	-	5	20	mV	10mA < IOUT < 200mA

●**Electrical Characteristics (BD750L2EFJ/FP/FP3-C)**

(Unless otherwise specified, -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA, Reference value: Ta=25°C)

Parameter	Symbol	Limit			Unit	Conditions
		Min	Typ	Max		
Bias current	Ib	-	6	15	μA	
Output voltage	VOUT	4.9	5.0	5.1	V	8V < VCC < 16V 0mA < IOUT < 100mA
Dropout voltage	ΔVd	-	0.4	0.7	V	VCC=VOUT×0.95, IOUT=200mA
Ripple rejection	R.R.	50	60	-	dB	f=120Hz, ein=1Vrms, IOUT=100mA
Line regulation	Reg I	-	5	20	mV	8V < VCC < 16V
Load regulation	Reg L	-	5	20	mV	10mA < IOUT < 200mA

© 2013 ROHM Co., Ltd. All rights reserved.

●Typical Performance Curves

■BD733L2EFJ/FP/FP3-C Reference data

Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

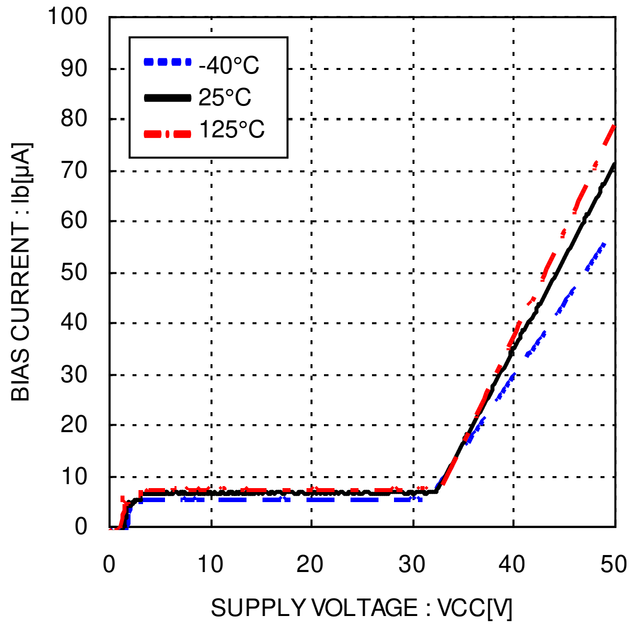


Figure 5. Bias current

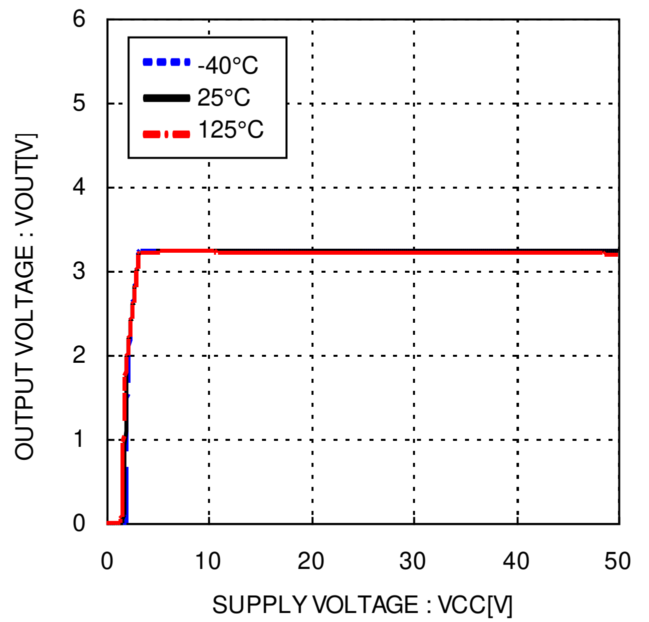


Figure 6. Output voltage vs. Supply voltage
IOUT=10mA

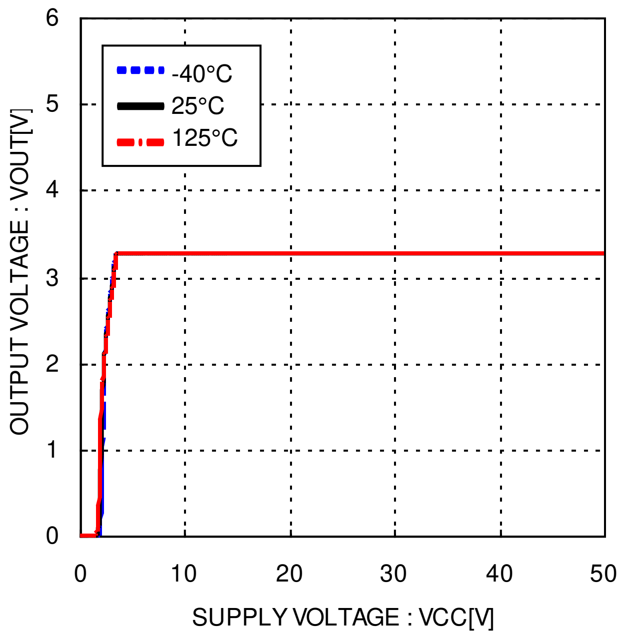


Figure 7. Output voltage vs. Supply voltage
IOUT=100mA

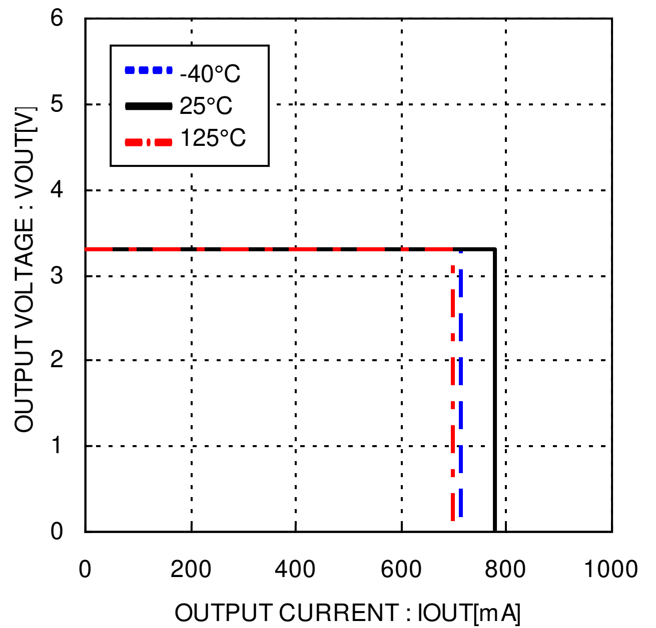


Figure 8. Output voltage vs. Load

© 2013 ROHM Co., Ltd. All rights reserved.

●**Typical Performance Curves – continued**

■BD733L2EFJ/FP/FP3-C Reference data

Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

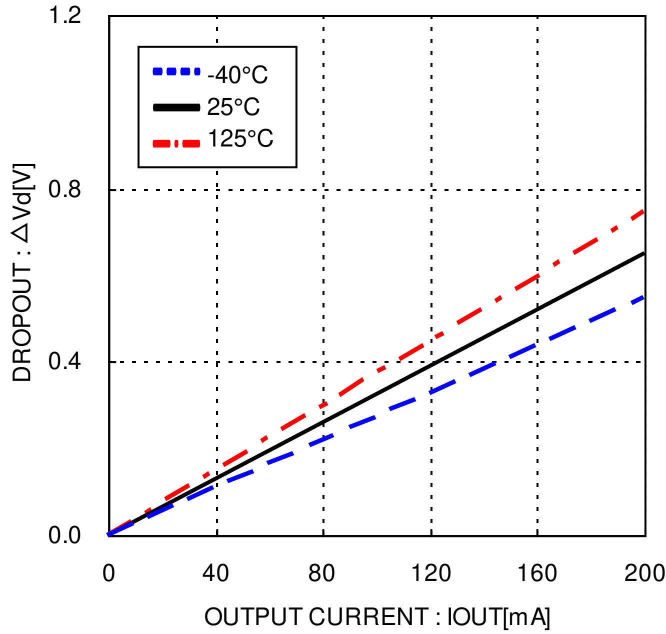


Figure 9. Dropout voltage

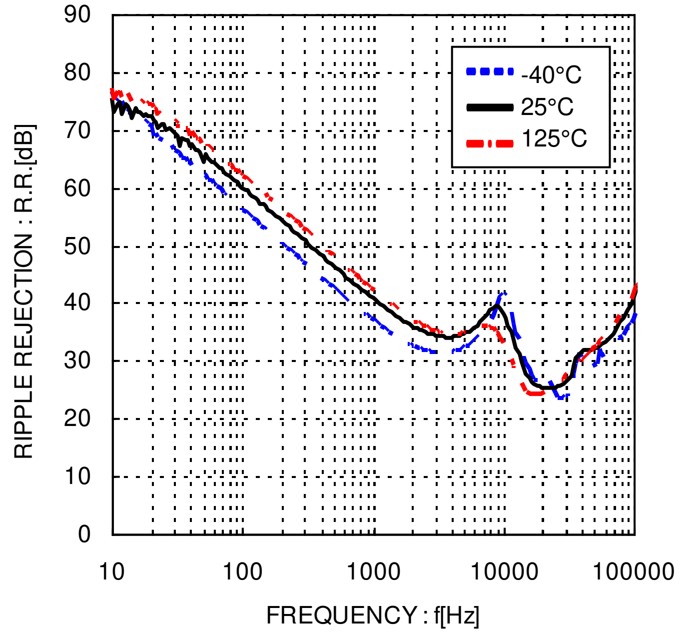


Figure 10. Ripple rejection
(ein=1Vrms,IOUT=100mA)

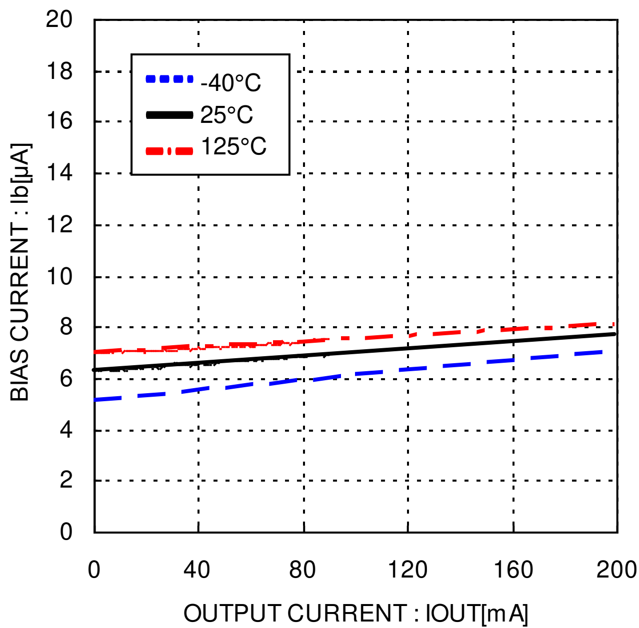


Figure 11. Total supply current vs. Load

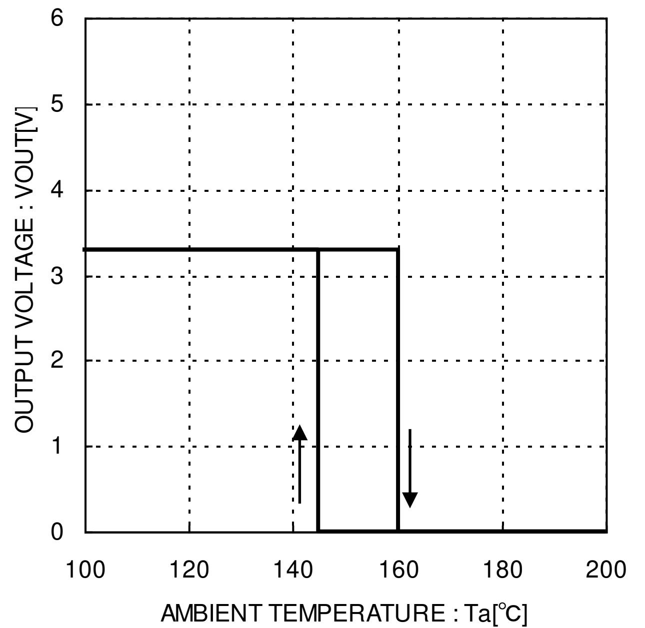


Figure 12. Thermal shutdown
(Output voltage vs. Temperature)

© 2013 ROHM Co., Ltd. All rights reserved.

●Typical Performance Curves – continued

■BD733L2EFJ/FP/FP3-C Reference data

Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

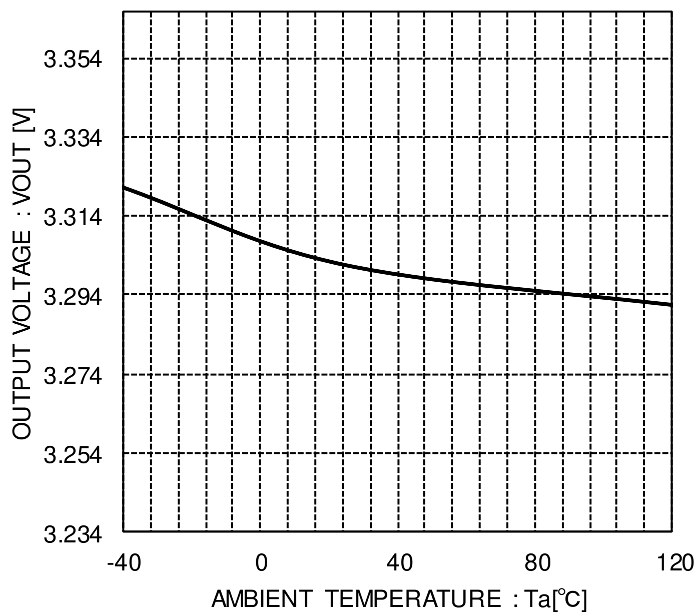


Figure 13. Output voltage vs. Temperature

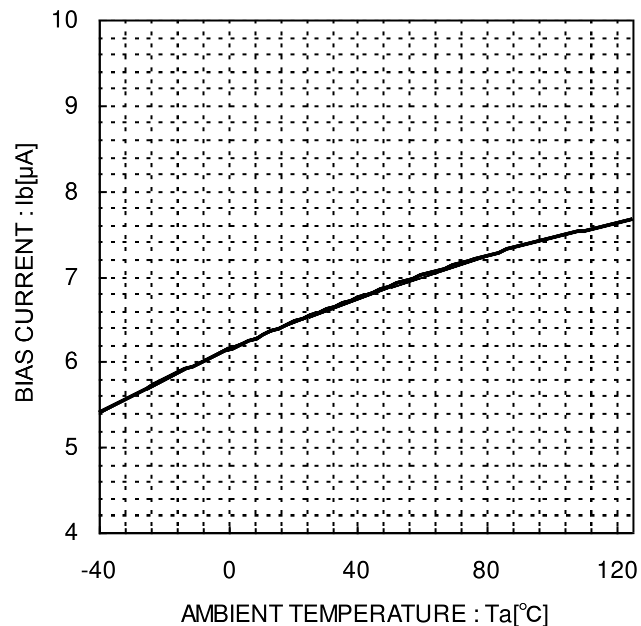


Figure 14. Bias current vs. Temperature

© 2013 ROHM Co., Ltd. All rights reserved.

●Typical Performance Curves – continued

■BD750L2EFJ/FP/FP3-C Reference data

Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

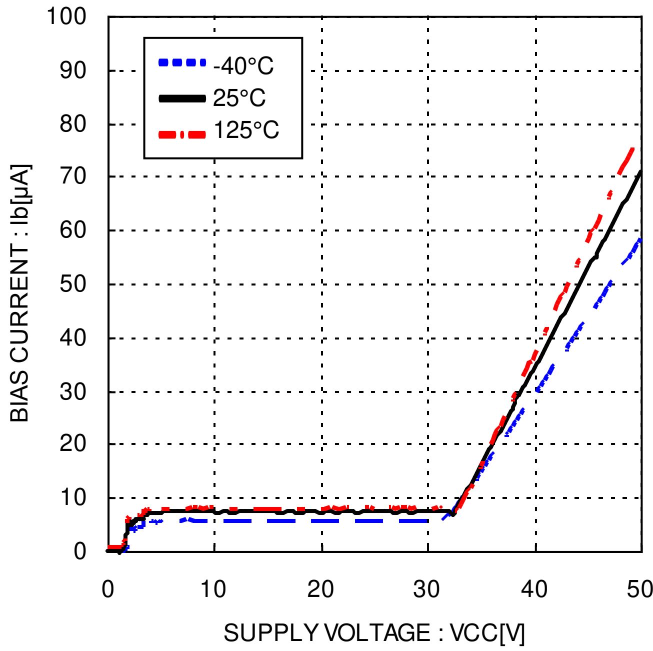


Figure 15. Bias current

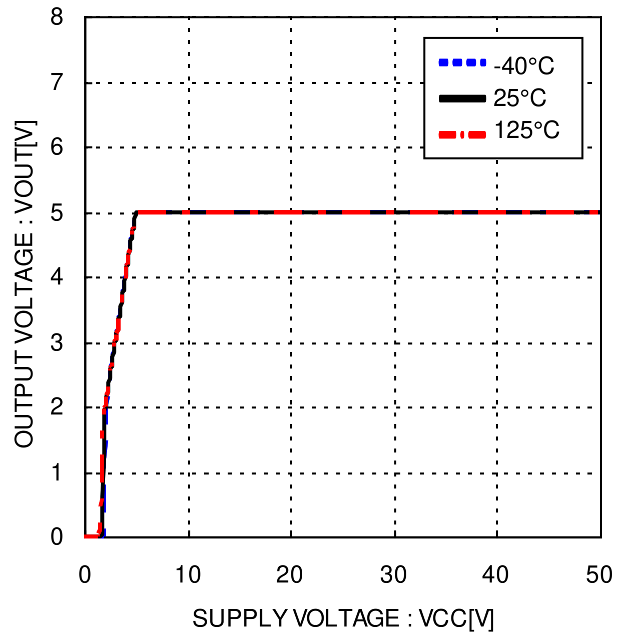


Figure 16. Output voltage vs. Supply voltage

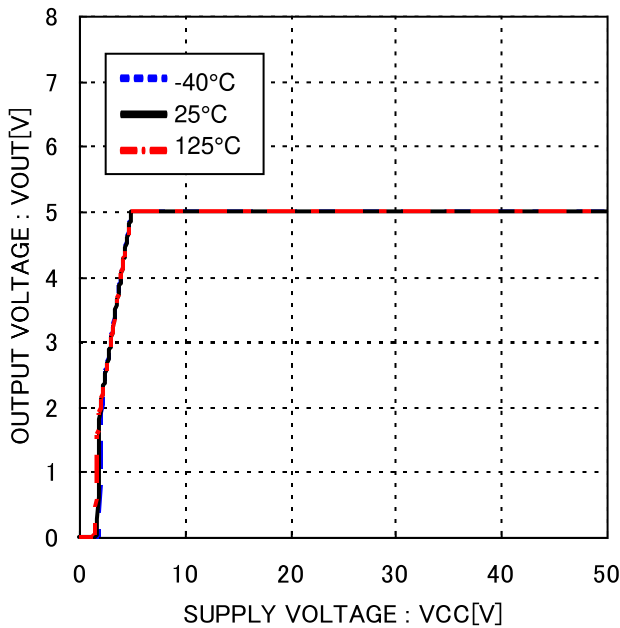


Figure 17. Output voltage vs. Supply voltage
IOUT=100mA

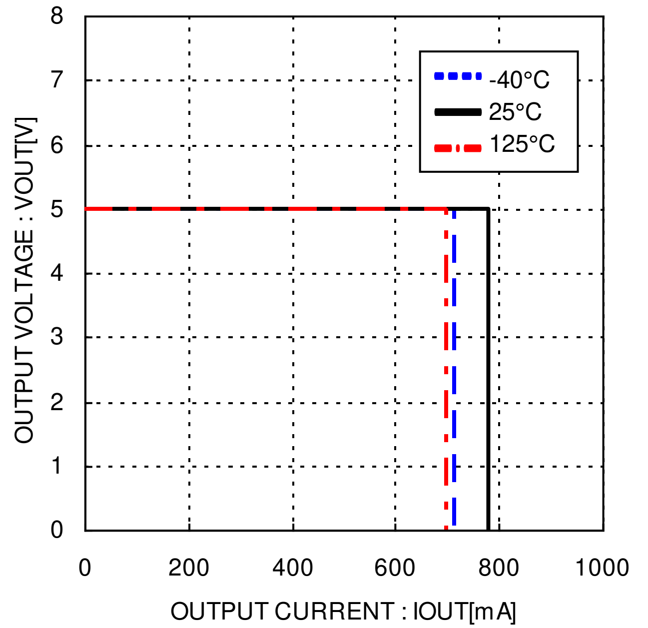


Figure 18. Output voltage vs. Load

© 2013 ROHM Co., Ltd. All rights reserved.

●**Typical Performance Curves – continued**

■BD750L2EFJ/FP/FP3-C Reference data

Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

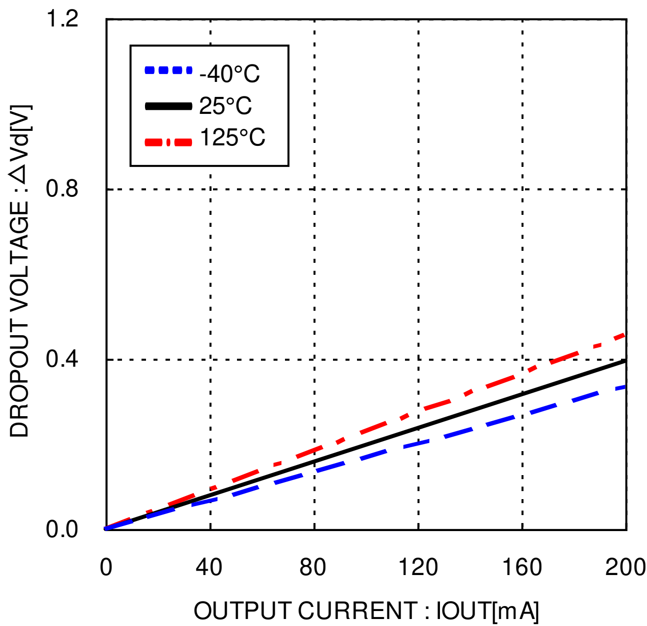


Figure 19. Dropout voltage

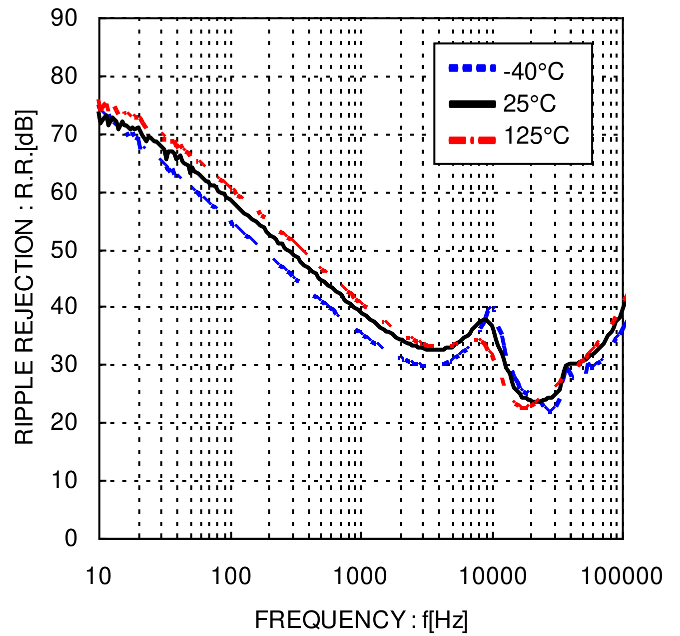


Figure 20. Ripple rejection
(ein=1Vrms,IOUT=100mA)

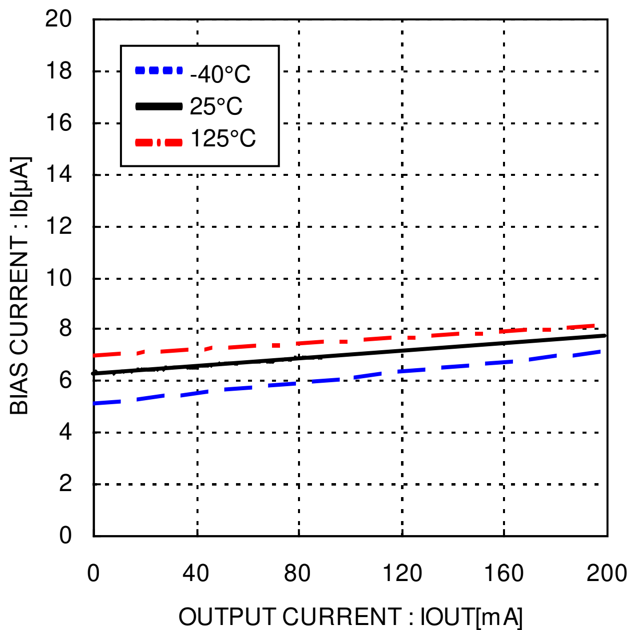


Figure 21. Total supply current vs. Load

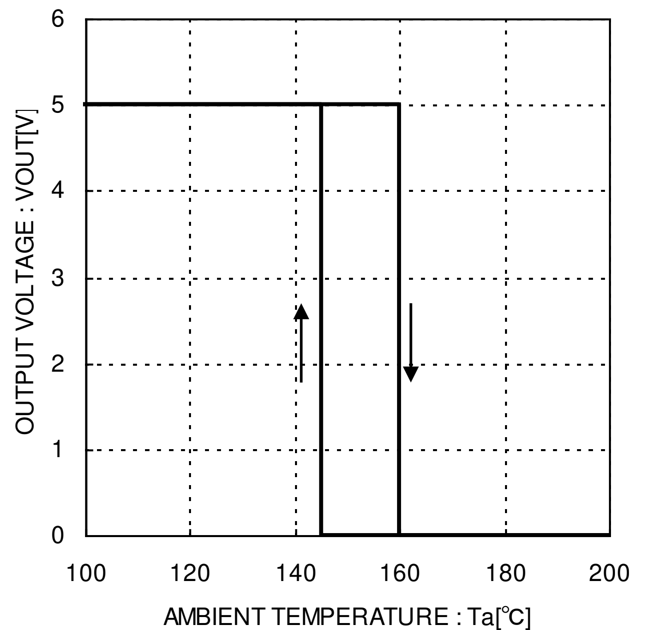


Figure 22. Thermal shutdown
(Output voltage vs. Temperature)

© 2013 ROHM Co., Ltd. All rights reserved.

● **Typical Performance Curves – continued**

■BD750L2EFJ/FP/FP3-C Reference data

Unless otherwise specified: -40 < Ta < +125°C, VCC=13.5V, IOUT=0mA

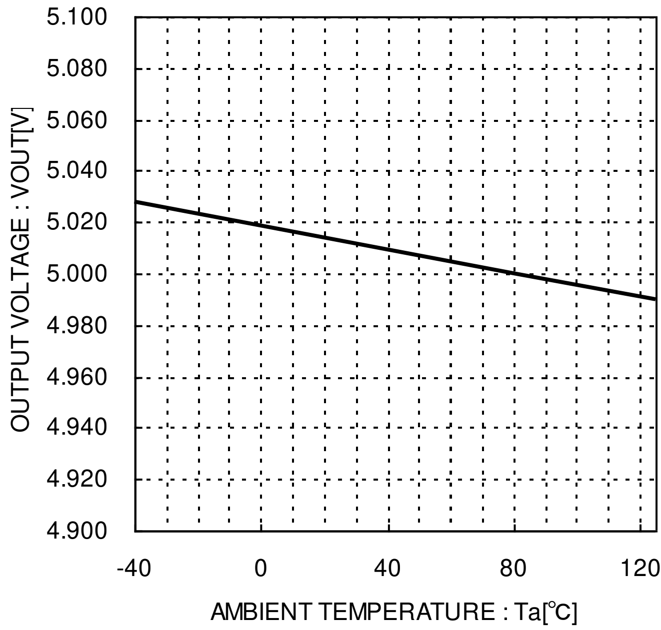


Figure 23. Output voltage vs. Temperature

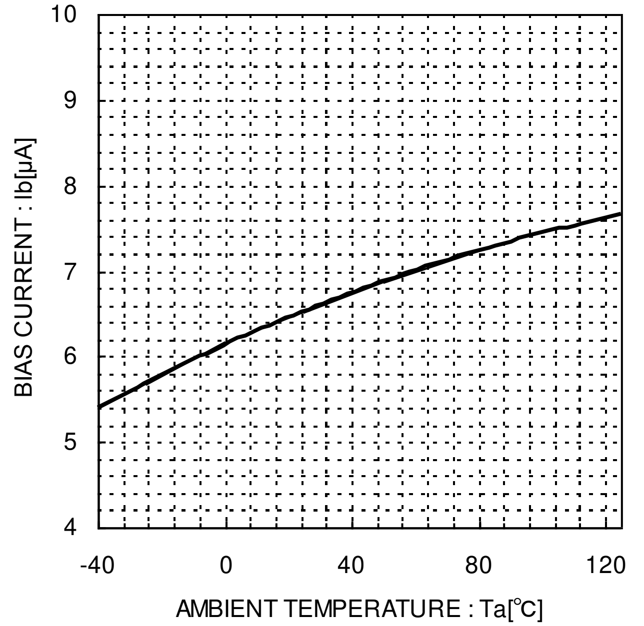
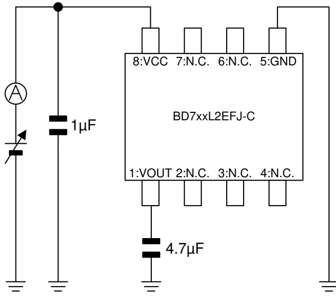


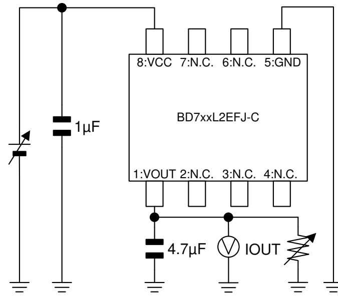
Figure 24. Bias current vs. Temperature

© 2013 ROHM Co., Ltd. All rights reserved.

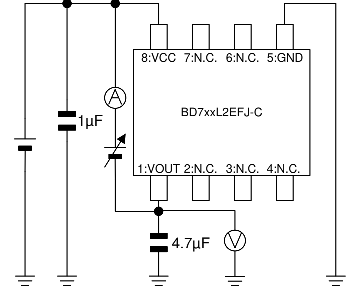
●**Measurement Circuit (BD7xxL2EFJ-C Series) HTSOP-J8**



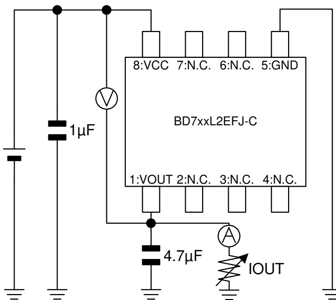
Measurement setup for Figure 5, 14, 15, 24



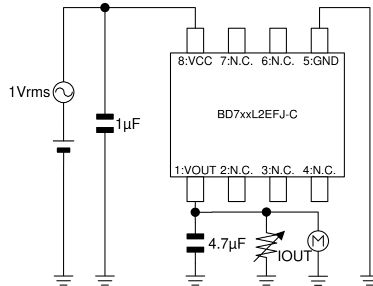
Measurement setup for
Figure 6, 7, 12, 13, 16, 17, 22, 23



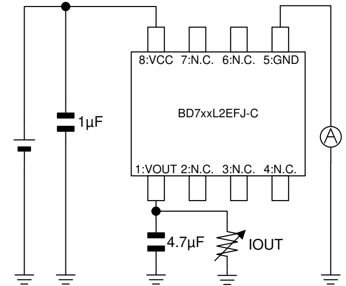
Measurement setup for Figure 8, 18



Measurement setup for Figure 9, 19

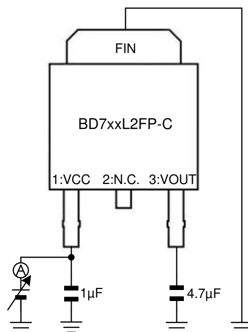


Measurement setup for Figure 10, 20

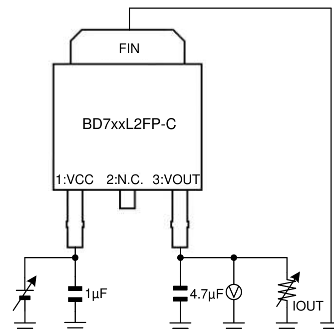


Measurement setup for Figure 11, 21

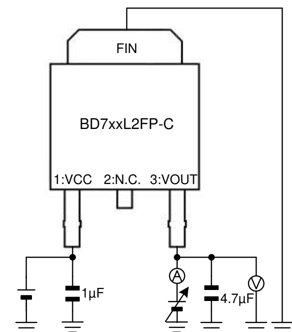
●**Measurement Circuit (BD7xxL2FP-C Series) TO252-3**



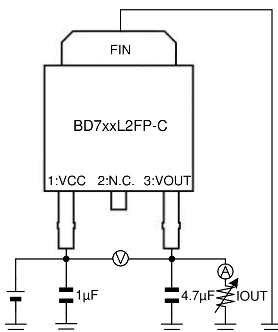
Measurement setup for Figure 5, 14, 15, 24



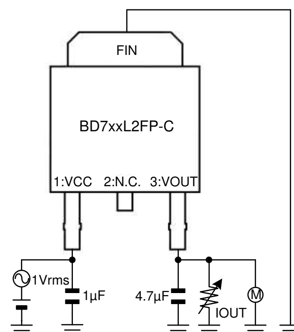
Measurement setup for
Figure 6, 7, 12, 13, 16, 17, 22, 23



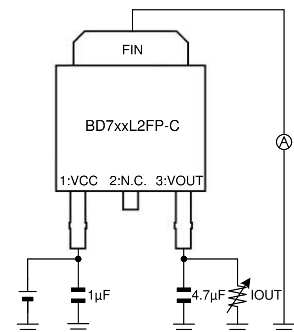
Measurement setup for Figure 8, 18



Measurement setup for Figure 9, 19



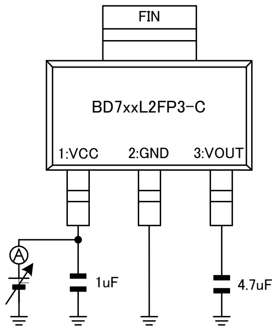
Measurement setup for Figure 10, 20



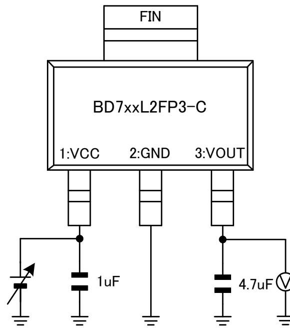
Measurement setup for Figure 11, 21

© 2013 ROHM Co., Ltd. All rights reserved.

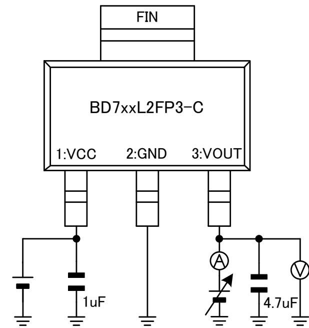
●**Measurement Circuit (BD7xxL2FP3-C Series) SOT223-4(F)**



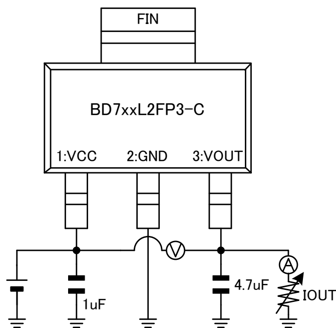
Measurement setup for Figure 5, 14, 15, 24



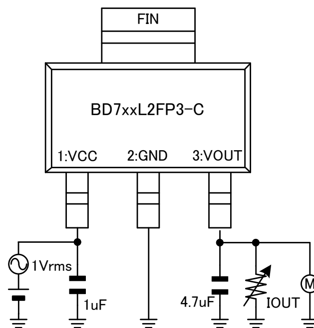
Measurement setup for
Figure 6, 7, 12, 13, 16, 17, 22, 23



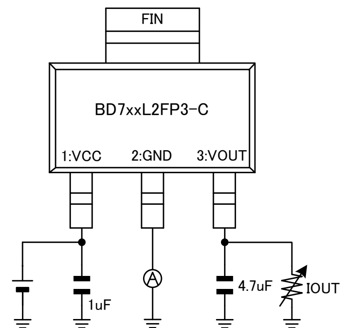
Measurement setup for Figure 8, 18



Measurement setup for Figure 9, 19



Measurement setup for Figure 10, 20



Measurement setup for Figure 11, 21

© 2013 ROHM Co., Ltd. All rights reserved.

●Selection of Components Externally Connected

・VCC pin

Insert capacitors with a capacitance of 0.1µF or higher between the VCC and GND pin. Choose the capacitance according to the line between the power smoothing circuit and the VCC pin. Selection of the capacitance also depends on the application. Verify the application and allow for sufficient margins in the design. We recommend using a capacitor with excellent voltage and temperature characteristics.

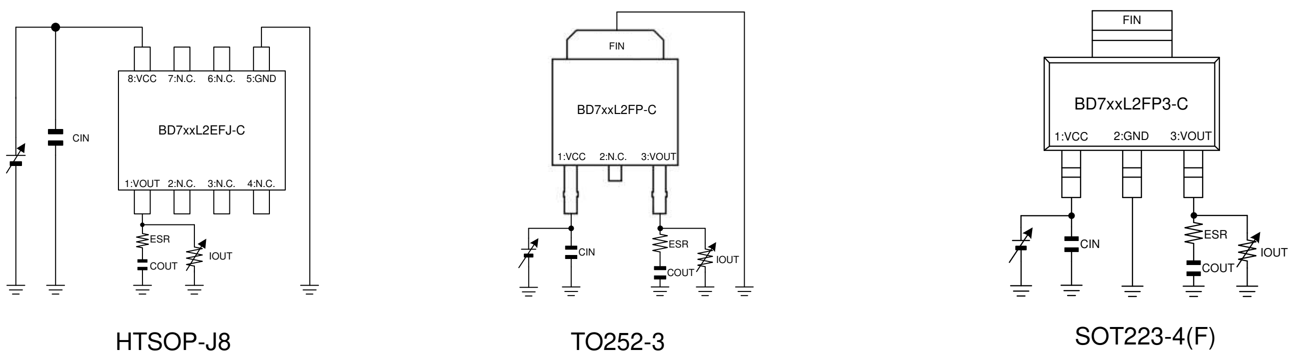
・Output pin capacitor

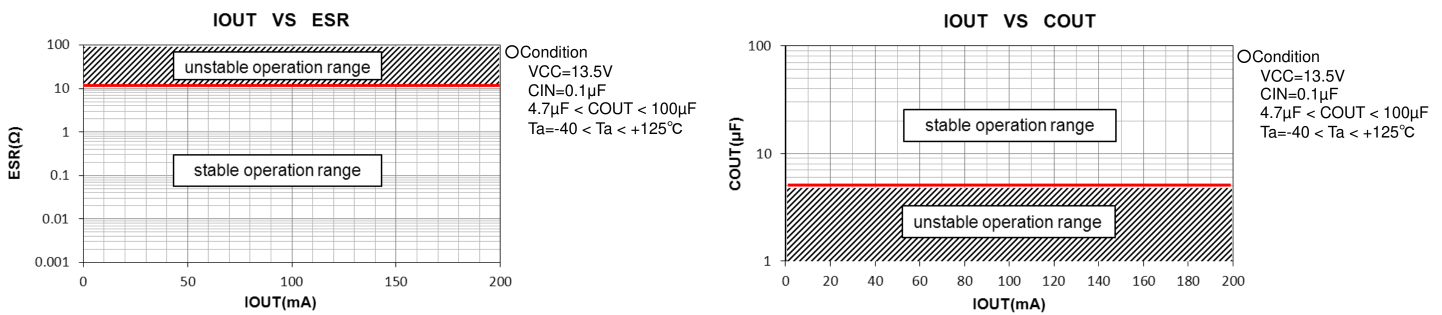
In order to prevent oscillation, a capacitor needs to be placed between the output pin and GND pin. We recommend using a capacitor with a capacitance of 4.7µF or higher. Electrolytic, tantalum and ceramic capacitors can be used. When selecting the capacitor ensure that the capacitance of 4.7µF or higher is maintained at the intended applied voltage and temperature range. Due to changes in temperature the capacitor's capacitance can fluctuate possibly resulting in oscillation. For selection of the capacitor refer to the IOUT vs. ESR data. The stable operation range given in the reference data is based on the standalone IC and resistive load. For actual applications the stable operating range is influenced by the PCB impedance, input supply impedance and load impedance. Therefore verification of the final operating environment is needed.

When selecting a ceramic type capacitor, we recommend using X5R, X7R or better with excellent temperature and DC-biasing characteristics and high voltage tolerance.

Also, in case of rapidly changing input voltage and load current, select the capacitance in accordance with verifying that the actual application meets with the required specification.

●Measurement setup





© 2013 ROHM Co., Ltd. All rights reserved.

●Power Dissipation

■HTSOP-J8

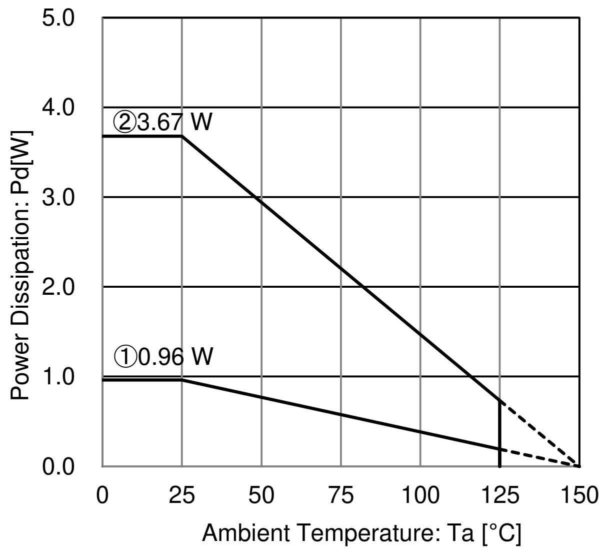


Figure 25. HTSOP-J8 Package Data

IC mounted on ROHM standard board based on JEDEC.

① : 1 - layer PCB
(Copper foil area on the reverse side of PCB: 0 mm x 0 mm)
Board material: FR4
Board size: 114.3 mm x 76.2 mm x 1.57 mmt
Mount condition: PCB and exposed pad are soldered.
Top copper foil: ROHM recommended
footprint + wiring to measure, 2 oz. copper.

② : 4 - layer PCB
(2 inner layers and Copper foil area on the reverse side of PCB:
74.2 mm x 74.2 mm)
Board material: FR4
Board size: 114.3 mm x 76.2 mm x 1.60 mmt
Mount condition: PCB and exposed pad are soldered.
Top copper foil: ROHM recommended
footprint + wiring to measure, 2 oz. copper.
2 inner layers copper foil area of PCB
: 74.2 mm x 74.2 mm, 1 oz. copper.
Copper foil area on the reverse side of PCB
: 74.2 mm x 74.2 mm, 2 oz. copper.

Condition①: θ_{JA} = 130 °C / W, Ψ_{JT} (top center) = 15 °C / W
Condition②: θ_{JA} = 34 °C / W, Ψ_{JT} (top center) = 7 °C / W

■TO252-3

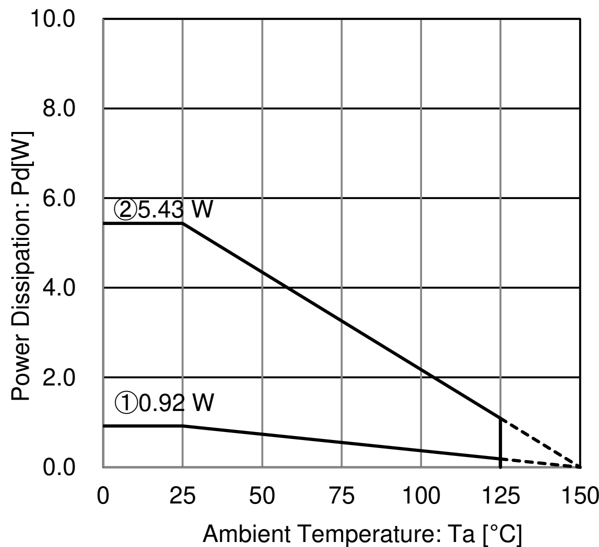


Figure 26. TO252-3 Package Data

IC mounted on ROHM standard board based on JEDEC.

① : 1 - layer PCB
(Copper foil area on the reverse side of PCB: 0 mm x 0 mm)
Board material: FR4
Board size: 114.3 mm x 76.2 mm x 1.57 mmt
Mount condition: PCB and exposed pad are soldered.
Top copper foil: ROHM recommended
footprint + wiring to measure, 2 oz. copper.

② : 4 - layer PCB
(2 inner layers and Copper foil area on the reverse side of PCB:
74.2 mm x 74.2 mm)
Board material: FR4
Board size: 114.3 mm x 76.2 mm x 1.60 mmt
Mount condition: PCB and exposed pad are soldered.
Top copper foil: ROHM recommended
footprint + wiring to measure, 2 oz. copper.
2 inner layers copper foil area of PCB
: 74.2 mm x 74.2 mm, 1 oz. copper.
Copper foil area on the reverse side of PCB
: 74.2 mm x 74.2 mm, 2 oz. copper.

Condition①: θ_{JA} = 136 °C / W, Ψ_{JT} (top center) = 17 °C / W
Condition②: θ_{JA} = 23 °C / W, Ψ_{JT} (top center) = 3 °C / W

© 2013 ROHM Co., Ltd. All rights reserved.

■SOT223-4(F)

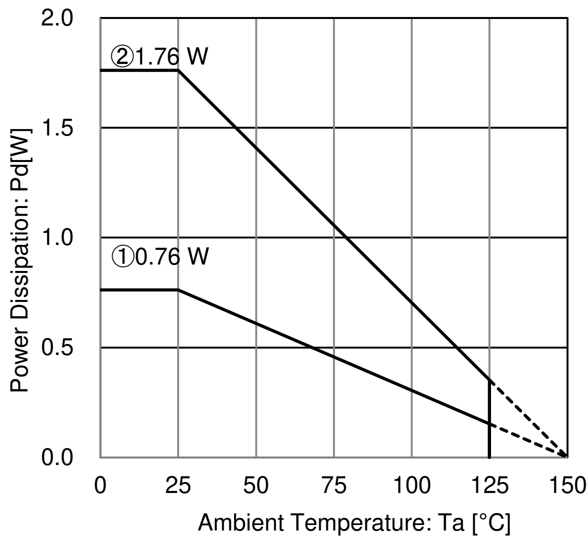


Figure 27. SOT223-4(F) Package Data

IC mounted on ROHM standard board based on JEDEC.

① : 1 - layer PCB
(Copper foil area on the reverse side of PCB: 0 mm x 0 mm)
Board material: FR4
Board size: 114.3 mm x 76.2 mm x 1.57 mm
Mount condition: PCB and exposed pad are soldered.
Top copper foil: ROHM recommended
footprint + wiring to measure, 2 oz. copper.

② : 4 - layer PCB
(2 inner layers and Copper foil area on the reverse side of PCB:
74.2 mm x 74.2 mm)
Board material: FR4
Board size: 114.3 mm x 76.2 mm x 1.60 mm
Mount condition: PCB and exposed pad are soldered.
Top copper foil: ROHM recommended
footprint + wiring to measure, 2 oz. copper.
2 inner layers copper foil area of PCB
: 74.2 mm x 74.2 mm, 1 oz. copper.
Copper foil area on the reverse side of PCB
: 74.2 mm x 74.2 mm, 2 oz. copper.

Condition①: θ_{JA} = 164 °C / W, Ψ_{JT} (top center) = 20 °C / W
Condition②: θ_{JA} = 71 °C / W, Ψ_{JT} (top center) = 14 °C / W

© 2013 ROHM Co., Ltd. All rights reserved.

Refer to the heat mitigation characteristics illustrated in Figure 25 to Figure 27 when using the IC in an environment of $T_a \geq 25°C$. The characteristics of the IC are greatly influenced by the operating temperature, and it is necessary to operate under the maximum junction temperature Timax.
Even if the ambient temperature Ta is at 25°C it is possible that the junction temperature Tj reaches high temperatures. Therefore, the IC should be operated within the power dissipation range.

The following method is used to calculate the power consumption Pc (W)

$$Pc=(VCC-VOUT)\times IOUT+VCC\times Ib$$

Power dissipation Pd ≥ Pc

VCC : Input voltage
VOUT : Output voltage
IOUT : Load current
Ib : Bias current
Ishort : Shorted current

The load current Lo is obtained by operating the IC within the power dissipation range.

$$IOUT \leq \frac{Pd-VCC\times Ib}{VCC-VOUT}$$

(Refer to Figure 11 and Figure 21 for the Ib)

Thus, the maximum load current IOUTmax for the applied voltage VCC can be calculated during the thermal design process.

●HTSOP-J8

■Calculation example 1) with Ta=125°C, VCC=13.5V, VOUT=3.3V

$$IOUT \leq \frac{0.73-13.5\times Ib}{10.2}$$

IOUT ≤ 71.5mA (Ib: 6µA)

θja=34°C/W → -29.4mW/°C
25°C=3.67W → 125°C=0.73W

At Ta=125°C with Figure 25 ② condition, the calculation shows that ca 71.5mA of output current is possible at 10.2V potential difference across input and output.

■Calculation example 2) with Ta=125°C, VCC=13.5V, VOUT=5.0V

$$IOUT \leq \frac{0.73-13.5\times Ib}{8.5}$$

IOUT ≤ 85.8mA (Ib: 6µA)

θja=34°C/W → -29.4mW/°C
25°C=3.67W → 125°C=0.73W

At Ta=125°C with Figure 25 ② condition, the calculation shows that ca 85.8mA of output current is possible at 8.5V potential difference across input and output.

The thermal calculation shown above should be taken into consideration during the thermal design in order to keep the whole operating temperature range within the power dissipation range.
In the event of shorting (i.e. VOUT and GND pins are shorted) the power consumption Pc of the IC can be calculated as follows:

$$Pc=VCC\times(Ib+Ishort)$$

(Refer to Figure 8 and Figure 18 for the Ishort)

© 2013 ROHM Co., Ltd. All rights reserved.

●TO252-3

■Calculation example 3) with Ta=125°C, VCC=13.5V, VOUT=3.3V

$$IOUT \leq \frac{1.08 - 13.5 \times Ib}{10.2}$$

$IOUT \leq 105mA$ (Ib: 6µA)

(θja=23°C/W → -43.5mW/°C
25°C=5.43W → 125°C=1.08W)

At Ta=125°C with Figure 26 ② condition, the calculation shows that ca 105mA of output current is possible at 10.2V potential difference across input and output.

■Calculation example 4) with Ta=125°C, VCC=13.5V, VOUT=5.0V

$$IOUT \leq \frac{1.08 - 13.5 \times Ib}{8.5}$$

$IOUT \leq 127mA$ (Ib: 6µA)

(θja=23°C/W → -43.5mW/°C
25°C=5.43W → 125°C=1.08W)

At Ta=125°C with Figure 26 ② condition, the calculation shows that ca 127mA of output current is possible at 8.5V potential difference across input and output.

The thermal calculation shown above should be taken into consideration during the thermal design in order to keep the whole operating temperature range within the power dissipation range.
In the event of shorting (i.e. VOUT and GND pins are shorted) the power consumption Pc of the IC can be calculated as follows:

$Pc = VCC \times (Ib + Ishort)$ (Refer to Figure 8 and Figure 18 for the Ishort)

© 2013 ROHM Co., Ltd. All rights reserved.

●SOT223-4(F)

■Calculation example 5) with Ta=125°C, VCC=13.5V, VOUT=3.3V

$$IOUT \leq \frac{0.35 - 13.5 \times Ib}{10.2}$$

$$IOUT \leq 34.3mA \quad (Ib: 6\mu A)$$

θja=71°C/W → -14.1mW/°C
25°C=1.76W → 125°C=0.35W

At Ta=125°C with Figure 27 ② condition, the calculation shows that ca 34.3mA of output current is possible at 10.2V potential difference across input and output.

■Calculation example 6) with Ta=125°C, VCC=13.5V, VOUT=5.0V

$$IOUT \leq \frac{0.35 - 13.5 \times Ib}{8.5}$$

$$IOUT \leq 41.1mA \quad (Ib: 6\mu A)$$

θja=71°C/W → -14.1mW/°C
25°C=1.76W → 125°C=0.35W

At Ta=125°C with Figure 27 ② condition, the calculation shows that ca 41.1mA of output current is possible at 8.5V potential difference across input and output.

The thermal calculation shown above should be taken into consideration during the thermal design in order to keep the whole operating temperature range within the power dissipation range.
In the event of shorting (i.e. VOUT and GND pins are shorted) the power consumption Pc of the IC can be calculated as follows:

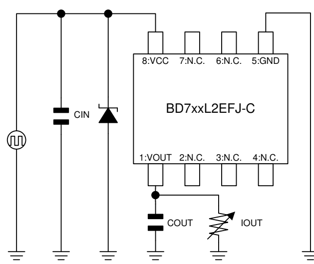
Pc=VCC×(Ib+Ishort) (Refer to Figure 8 and Figure 18 for the Ishort)

© 2013 ROHM Co., Ltd. All rights reserved.

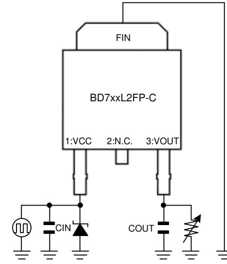
● **Application Examples**

・Applying positive surge to the VCC pin

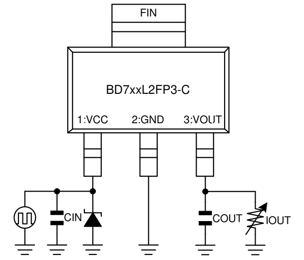
If the possibility exists that surges higher than 50V will be applied to the VCC pin, a zenar diode should be placed between the VCC pin and GND pin as shown in the figure below.



HTSOP-J8



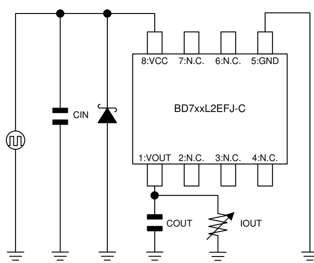
TO252-3



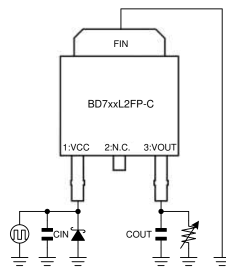
SOT223-4(F)

・Applying negative surge to the VCC pin

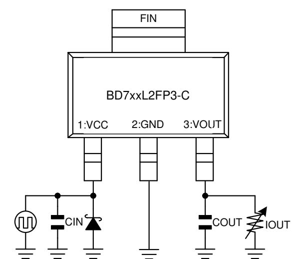
If the possibility exists that negative surges lower than the GND are applied to the VCC pin, a Shottky diode should be place between the VCC pin and GND pin as shown in the figure below.



HTSOP-J8



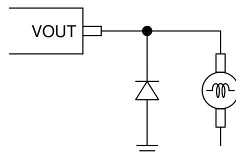
TO252-3



SOT223-4(F)

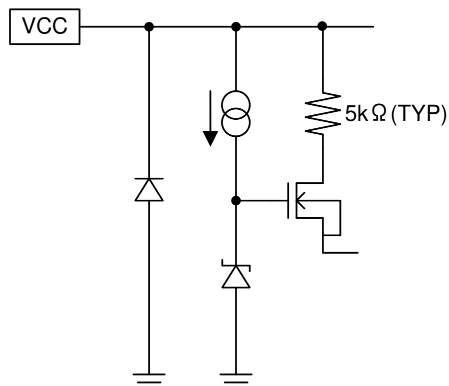
・Implementing a protection diode

If the possibility exists that a large inductive load is connected to the output pin resulting in back-EMF at time of startup and shutdown, a protection diode should be placed as shown in the figure below.

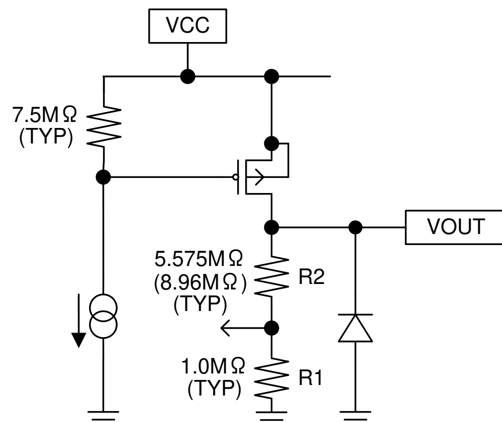


● **I/O equivalence circuits**

○Input terminal



○Output terminal *inside of () shows 5V



© 2013 ROHM Co., Ltd. All rights reserved.

●**Operational Notes**

1) Absolute maximum ratings

Exceeding the absolute maximum rating for supply voltage, operating temperature or other parameters can result in damages to or destruction of the chip. In this event it also becomes impossible to determine the cause of the damage (e.g. short circuit, open circuit, etc.). Therefore, if any special mode is being considered with values expected to exceed the absolute maximum ratings, implementing physical safety measures, such as adding fuses, should be considered.

2) The electrical characteristics given in this specification may be influenced by conditions such as temperature, supply voltage and external components. Transient characteristics should be sufficiently verified.

3) GND electric potential

Keep the GND pin potential at the lowest (minimum) level under any operating condition. Furthermore, ensure that, including the transient, none of the pin's voltages are less than the GND pin voltage.

4) GND wiring pattern

When both a small-signal GND and a high current GND are present, single-point grounding (at the set standard point) is recommended. This in order to separate the small-signal and high current patterns and to ensure that voltage changes stemming from the wiring resistance and high current do not cause any voltage change in the small-signal GND. Similarly, care must be taken to avoid wiring pattern fluctuations in any connected external component GND.

5) Inter-pin shorting and mounting errors

Ensure that when mounting the IC on the PCB the direction and position are correct. Incorrect mounting may result in damaging the IC. Also, shorts caused by dust entering between the output, input and GND pin may result in damaging the IC.

6) Inspection using the set board

The IC needs to be discharged after each inspection process as, while using the set board for inspection, connecting a capacitor to a low-impedance pin may cause stress to the IC. As a protection from static electricity, ensure that the assembly setup is grounded and take sufficient caution with transportation and storage. Also, make sure to turn off the power supply when connecting and disconnecting the inspection equipment.

7) Thermal design

The power dissipation under actual operating conditions should be taken into consideration and a sufficient margin should be allowed for in the thermal design. On the reverse side of the package this product has an exposed heat pad for improving the heat dissipation. Use both the front and reverse side of the PCB to increase the heat dissipation pattern as far as possible. The amount of heat generated depends on the voltage difference across the input and output, load current, and bias current. Therefore, when actually using the chip, ensure that the generated heat does not exceed the Pd rating. Should by any condition the maximum junction temperature rating be exceeded by the temperature increase of the chip, it may result in deterioration of the properties of the chip. The thermal impedance in this specification is based on recommended PCB and measurement condition by JEDEC standard. Verify the application and allow sufficient margins in the thermal design.

(Tjmax: maximum junction temperature=150°C, Ta: ambient temperature (°C), θja: junction-to-ambient thermal resistance (°C/W), Pd: power dissipation rating (W), Pc: power consumption (W), VCC: input voltage, VOUT: output voltage, IOUT: load current, Ib: bias current)

Power dissipation rating Pd (W)=(Tjmax－Ta)/θja
Power consumption Pc (W)=(VCC-VOUT)×IOUT＋VCC×Ib

8) Rapid variation in VCC voltage and load current

In case of a rapidly changing input voltage, transients in the output voltage might occur due to the use of a MOSFET as output transistor. Although the actual application might be the cause of the transients, the IC input voltage, output current and temperature are also possible causes. In case problems arise within the actual operating range, use countermeasures such as adjusting the output capacitance.

© 2013 ROHM Co., Ltd. All rights reserved.

9) Minute variation in output voltage

In case of using an application susceptible to minute changes to the output voltage due to noise, changes in input and load current, etc., use countermeasures such as implementing filters.

10) Overcurrent protection circuit

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

11) Thermal shutdown (TSD)

This IC incorporates and integrated thermal shutdown circuit to prevent heat damage to the IC. Normal operation should be within the power dissipation rating, if however the rating is exceeded for a continued period, the junction temperature (Tj) will rise and the TSD circuit will be activated and turn all output pins OFF. After the Tj falls below the TSD threshold the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

12) In some applications, the VCC and pin potential might be reversed, possibly resulting in circuit internal damage or damage to the elements. For example, while the external capacitor is charged, the VCC shorts to the GND. Use a capacitor with a capacitance with less than 1000µF. We also recommend using reverse polarity diodes in series or a bypass between all pins and the VCC pin.

13) This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements.

For example, in case a resistor and a transistor are connected to the pins as shown in the figure below then:

○ The P/N junction functions as a parasitic diode when GND > pin A for the resistor, or GND > pin B for the transistor.

○ Also, when GND > pin B for the transistor (NPN), the parasitic diode described above combines with the N layer of the other adjacent elements to operate as a parasitic NPN transistor.

Parasitic diodes inevitably occur in the structure of the IC. Their operation can result in mutual interference between circuits and can cause malfunctions and, in turn, physical damage to or destruction of the chip. Therefore do not employ any method in which parasitic diodes can operate such as applying a voltage to an input pin that is lower than the (P substrate) GND.

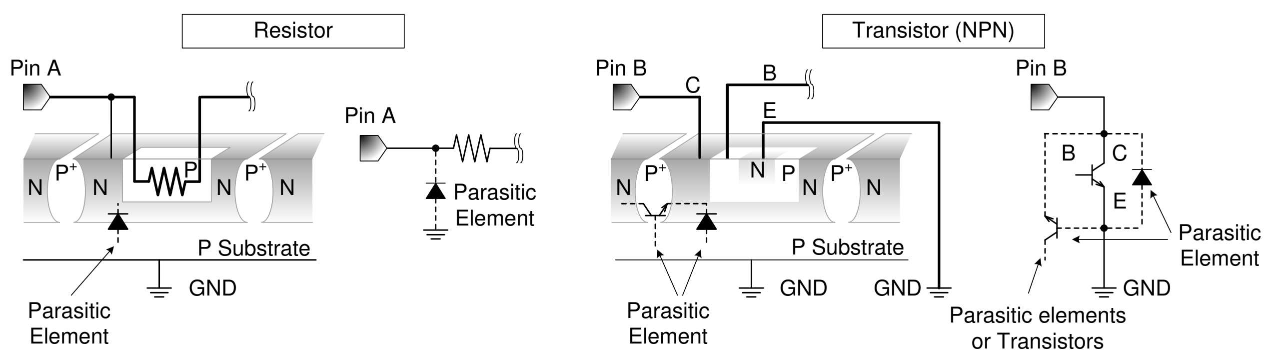
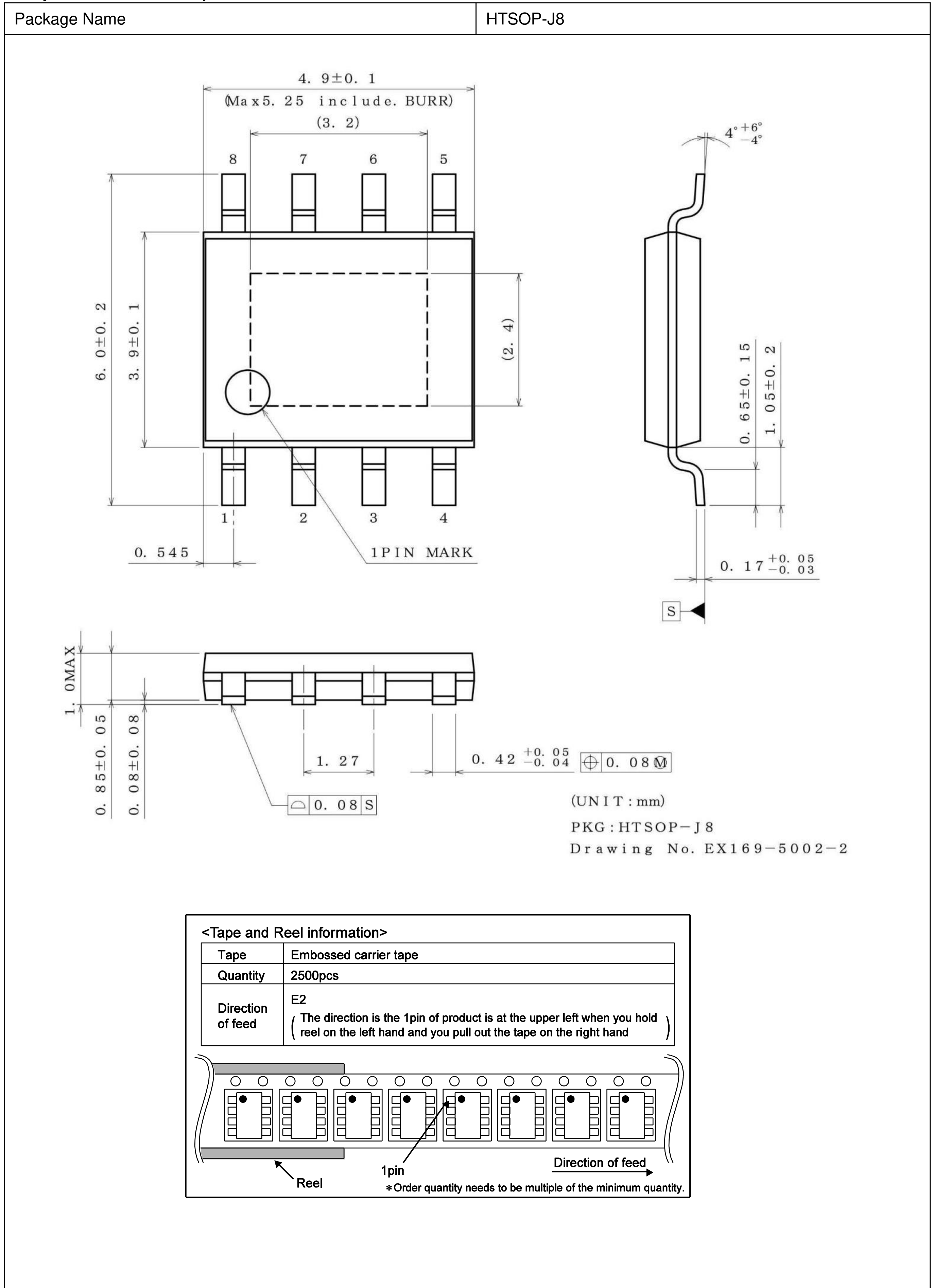


Figure 28. Example of the Parasitic Device Structures

© 2013 ROHM Co., Ltd. All rights reserved.

●Physical Dimension, Tape and Reel Information

Package Name	HTSOP-J8



<Tape and Reel information>

Tape	Embossed carrier tape
Quantity	2500pcs
Direction of feed	E2 (The direction is the 1pin of product is at the upper left when you hold reel on the left hand and you pull out the tape on the right hand)

© 2013 ROHM Co., Ltd. All rights reserved.